A THIN-FILM OPTO-ELECTRONIC DEVICE AND A METHOD OF MAKING IT

Stalmans et al.
Atty Docket: IMEC232.001DV1 Appl. No.: Unknown

1/4

Figure 1

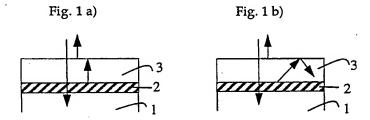


Figure 2

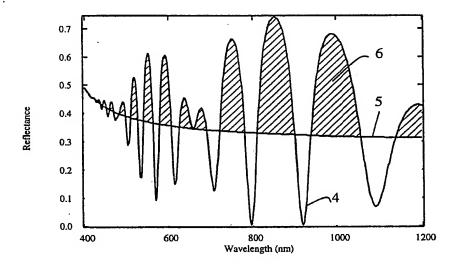
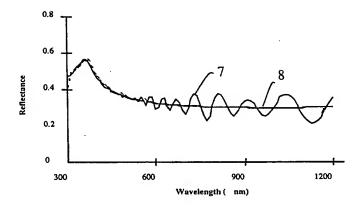


Figure 3



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Appl. No.: Unknown

Stalmans et al.
Atty Docket: IMEC232.001DV1

2/4

Figure 4

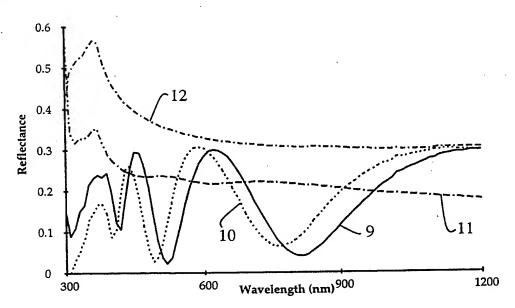


Figure 5

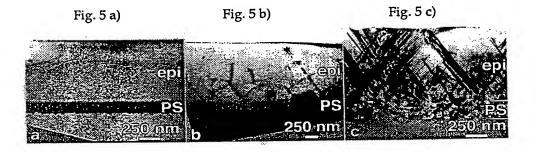


Figure 6

Temperature (°C)	CVD on Si	CVD on PS
	(nm/min)	(nm/min)
725 °C	4 - 8	11
800 °C	60 - 100	100
850 °C	200	

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Stalmans et al.

Appl. No.: Unknown Atty Docket: IMEC232.001DV1

3/4

Figure 7

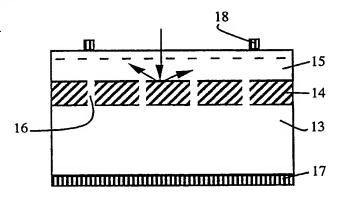
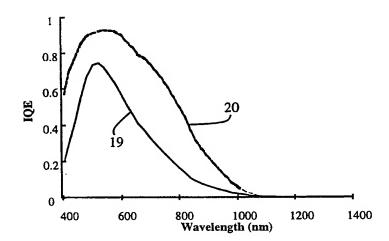


Figure 8



Stalmans et al,

Appl. No.: Unknown Atty Docket: IMEC232.001DV1

4/4

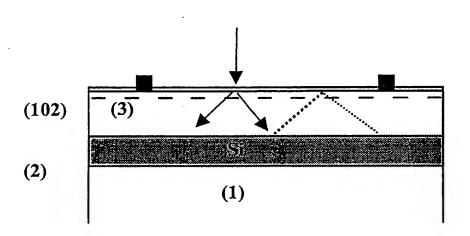


Figure 9

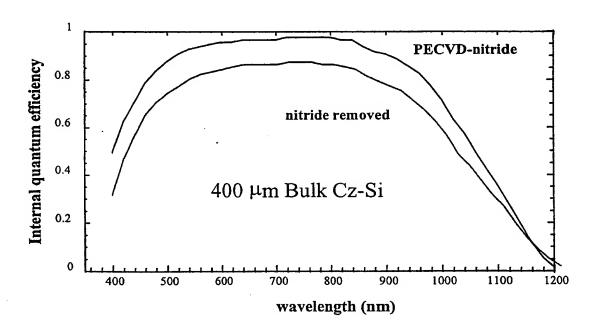


Figure 10